

Gate Driver with VReg and Two Point Regulator

DATASHEET

- 60mA/120mA MIN GATE DRIVE
- TWO POINT REGULATOR FOR SWITCHING CHARGE PUMP SUPPLY
- 3.3V OR 5V VOLTAGE REGULATOR
- **LOW STARTUP CURRENT**
- **UVLO PROTECTION**
- **2kV ESD PROTECTION**

DESCRIPTION

TD220 is a solution for micro-controller based offline applications. TD220 includes a two point regulator for power supply generation, a 3.3V (TD220) or 5V (TD221) linear regulator for the microcontroller supply, and a MOSFET driver.

APPLICATIONS

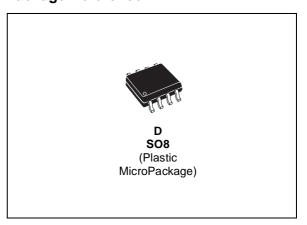
■ µC-BASED OFF-LINE APPLICATIONS

ORDER CODE

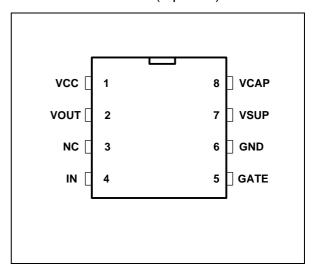
Part Number	Temperature	Package
l ait ivalliber	Range	D
TD220I	-25, +125°C	•
TD221I	-25, +125°C	•

Note: \mathbf{D} = Small Outline Package (SO) - also available in Tape & Reel (DT)

Package Reference

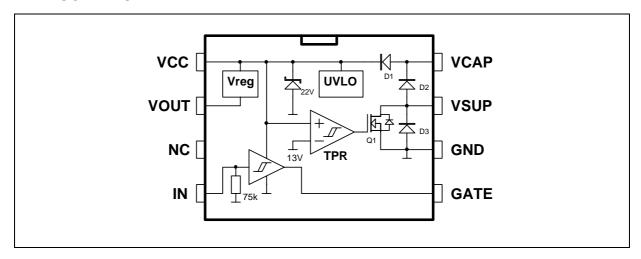


PIN CONNECTIONS (top view)



TD220/221 Block Diagram

1 BLOCK DIAGRAM



Pin Description

Name	Pin Number	Туре	Function
VCC	1	Power supply	Supply capacitor and startup resistor
VOUT	2	Analog output	+3.3V (TD220) or +5V (TD221) voltage regulator
IN	4	Digital input	Input signal for gate drive
GATE	5	Analog output	Gate drive output
GND	6	Power supply	Signal ground
VSUP	7	Power supply	Charge pump input
VCAP	8	Power supply	Capacitor for charge pump

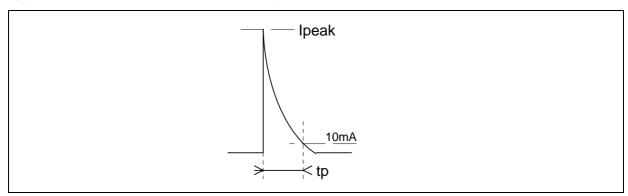
2 ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Icc<5mA)	-0.3 to selflimit	V
Vout	Voltage on GATE and VCAP pins	-0.3 to VCC+0.3	V
Vin	Voltage on IN and VOUT pins	-0.3 to 7	V
Isup	Continuous current in VSUP pin	-200 to 200	mA
lpeak	Peak current in VSUP pin (tp≤1μs, f≤150kHz, see waveform below)	-1.0 to 1.0	А
Pd	Power dissipation	500	mW
Tstg	Storage temperature	-55 to 150	°C
Tj	Maximum Junction Temperature	150	°C
Rhja	Thermal Resistance Junction-Ambient	150	°C/W
Rhjc	Thermal Resistance Junction-Case	40	°C/W
ESD	Electrostatic discharge (HBM)	2	kV

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
VCC	Supply Voltage	UVLO to 17	V
Isup	Continuous current in VSUP pin	0 to 200	mA
Ipeak	Peak current in VSUP pin (tp≤1μs, f≤150kHz, see waveform below)	-1.0 to 1.0	Α
Tj	Junction Temperature	-25 to 125	°C

Typical waveform of current in VSUP pin



3 ELECTRICAL CHARACTERISTICS

Tamb = 25°C, VCC=13V unless otherwise specified

d Voltage d Voltage	no load at any pin, Vin<1V Tamb=25°C -25°C <tj<125°c -25°c<tj<125°c="" 1nf="" 300khz="" active="" gate="" icc<5ma="" in="" load,="" signal="" tamb="25°C" uvlo="" vin="3.3V</th" vin<0.5v=""><th>20 1.8 1.0 0.5</th><th>0.7 5 160 22</th><th>1.0 1.2 6 230 24 2.1 1.3</th><th>mA mA mA μA μA V</th></tj<125°c>	20 1.8 1.0 0.5	0.7 5 160 22	1.0 1.2 6 230 24 2.1 1.3	mA mA mA μA μA V
d Voltage	Tamb=25°C -25°C <tj<125°c -25°c<tj<125°c="" 1nf="" 300khz="" active="" gate="" icc<5ma<="" in="" load,="" signal="" tamb="25°C" td="" uvlo=""><td>20 1.8 1.0</td><td>5 160</td><td>1.2 6 230 24 2.1 1.3</td><td>mA mA μA μA V</td></tj<125°c>	20 1.8 1.0	5 160	1.2 6 230 24 2.1 1.3	mA mA μA μA V
d Voltage	300kHz IN signal UVLO active Tamb=25°C -25°C <tj<125°c icc<5ma="" td="" vin<0.5v<=""><td>20 1.8 1.0</td><td>160</td><td>230 24 2.1 1.3</td><td>μΑ μΑ V</td></tj<125°c>	20 1.8 1.0	160	230 24 2.1 1.3	μΑ μΑ V
d Voltage	Tamb=25°C -25°C <tj<125°c icc<5ma="" td="" vin<0.5v<=""><td>1.8</td><td></td><td>24 2.1 1.3</td><td>μA V V V V V</td></tj<125°c>	1.8		24 2.1 1.3	μA V V V V V
d Voltage	Vin<0.5V	1.8	22	2.1	V V
d Voltage		1.0		1.3	V
d Voltage		1.0		1.3	V
					V
I .		0.5		20	+ -
ı				20	Δ.
1	Vin=3.3V				μΑ
				100	μΑ
					_1
	lout=10mA TD220 TD221	3.20 4.85	3.30	3.40 5.15	V
	lout change from 10mA to 25mA			50	mV
	Vout=1V	100		1	mA
ent	lout=10mA			250	ppm/°C
oad - Note 1	lout=10mA	0.1		1	μF
JVLO state	Vout=1V			10	μΑ
ote 1	f=100Hz f=10kHz	40 20			dB dB
	100Hz <f<100khz< td=""><td></td><td>1</td><td>1</td><td>mV</td></f<100khz<>		1	1	mV
3.1V)	Cout=1μF			0.1	ms
al value)	Cout=1μF		2		ms
				13.6	V
		12.4			V
	=VTPROn-VTPROff	0.23	0.29	0.35	V
			1	1.5	V
	3.1V)	f=10kHz 100Hz <f<100khz 8.1v)="" =vtpron-vtproff<="" al="" cout="1μF" td="" value)=""><td>f=10kHz 20 100Hz<f<100khz 0.23<="" 12.4="VTPROn-VTPROff" 3.1v)="" al="" cout="1μF" td="" value)=""><td> f=10kHz 20 100Hz<f<100khz 1="" td="" ="" <=""><td> f=10kHz 20 100Hz<f<100khz 0.1="" 1="" td="" ="" <=""></f<100khz></td></f<100khz></td></f<100khz></td></f<100khz>	f=10kHz 20 100Hz <f<100khz 0.23<="" 12.4="VTPROn-VTPROff" 3.1v)="" al="" cout="1μF" td="" value)=""><td> f=10kHz 20 100Hz<f<100khz 1="" td="" ="" <=""><td> f=10kHz 20 100Hz<f<100khz 0.1="" 1="" td="" ="" <=""></f<100khz></td></f<100khz></td></f<100khz>	f=10kHz 20 100Hz <f<100khz 1="" td="" ="" <=""><td> f=10kHz 20 100Hz<f<100khz 0.1="" 1="" td="" ="" <=""></f<100khz></td></f<100khz>	f=10kHz 20 100Hz <f<100khz 0.1="" 1="" td="" ="" <=""></f<100khz>

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
Gate Outp	ut		'			
VOL	Output low voltage	Igate=10mA			0.5	V
VOH	Output high voltage	Igate=-10mA	VCC-2.0			V
Isink	Output sink current	Vgate=6V Tj=25°C -25°C < Tj < 125°C	120	300		mA mA
Isrc	Output source current	Vgate=3V Tj=25°C -25°C < Tj < 125°C	60	150		mA mA
VOL2	Output low voltage in UVLO state	Vcc=6V, Igate=1mA			2	V
tgmin	Minimum output pulse width ¹	Cgate=10pF			80	ns
tpd	IN to GATE propagation delay			200		ns
Under Vol	tage Lockout (UVLO)					
UVLOH	UVLO top threshold				15	V
UVLOL	UVLO bottom threshold		7.8		8.7	V
Vhyst	UVLO Hysteresis	Vhyst=UVLOH-UVLOL	5			V

¹⁾ Not 100% tested. Guaranteed by design.

TD220/221 Timing Diagrams

4 TIMING DIAGRAMS

Fig. 1: Power up and power down

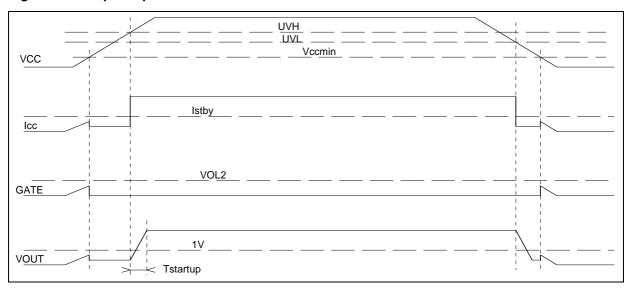
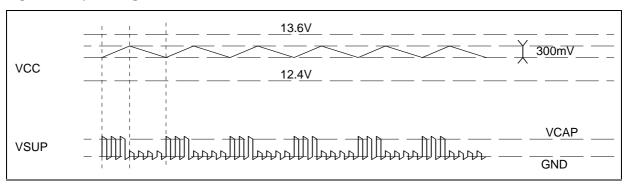
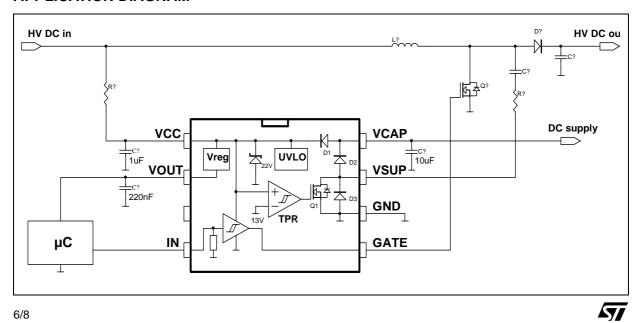


Fig. 2: Two point regulator



APPLICATION DIAGRAM



5 TYPICAL PERFORMANCE CURVES

Fig. 3: Supply Current vs Temperature

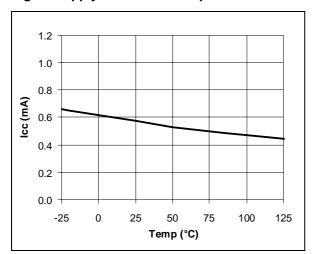


Fig. 4: Gate Drive Sink Current vs Temperature

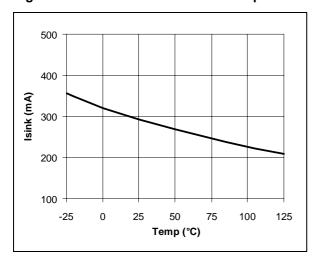


Fig. 5: Vreg Output Voltage vs Temperature

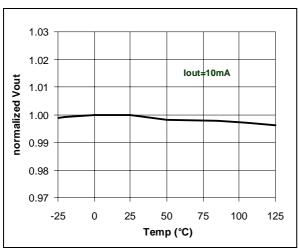


Fig. 6: Standby Current vs Temperature

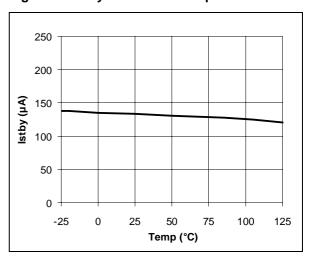
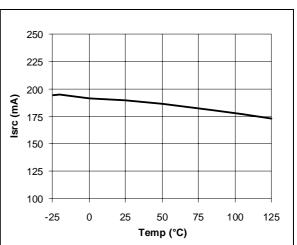


Fig. 7: Gate Drive Source Current vs Temp.

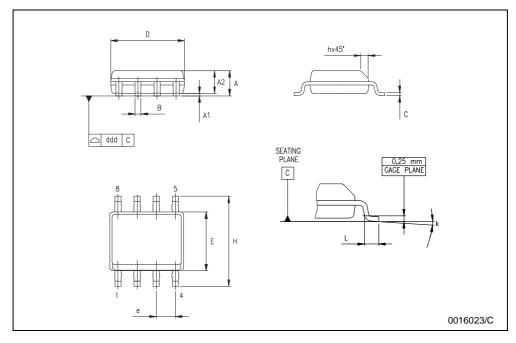


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6 PACKAGE MECHANICAL DATA

SO-8 MECHANICAL DATA

DIM.	mm.			inch			
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	1.35		1.75	0.053		0.069	
A1	0.10		0.25	0.04		0.010	
A2	1.10		1.65	0.043		0.065	
В	0.33		0.51	0.013		0.020	
С	0.19		0.25	0.007		0.010	
D	4.80		5.00	0.189		0.197	
E	3.80		4.00	0.150		0.157	
е		1.27			0.050		
Н	5.80		6.20	0.228		0.244	
h	0.25		0.50	0.010		0.020	
L	0.40		1.27	0.016		0.050	
k	8° (max.)						
ddd			0.1			0.04	



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